

Claim

in that order beginning with the silicon layer.

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4. (Amended) A semiconductor device according to Claim 1, wherein the metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer, and the metallic layer is a tungsten layer.

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C<sup>2</sup>

5. (Twice Amended) A semiconductor device with an MOS transistor whose gate electrode is provided as a stacked structure comprising a silicon layer and a metallic layer as the uppermost layer thereof, wherein a metal silicide layer is provided on the silicon layer side and a metal nitride layer is provided under the metallic layer side between the silicon layer and the metallic layer.

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C<sup>3</sup>

C<sup>4</sup>

8. (Amended) A semiconductor device according to Claim 5, wherein the metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer and the metallic layer is a tungsten layer.

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25. (Amended) A semiconductor device with complementary MOS transistors, each MOS transistor having a gate electrode, a source region and a drain region, wherein the gate electrode is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a metal nitride layer and a metallic layer, formed in that order beginning with the silicon layer.

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C<sup>5</sup>

28. (Amended) A semiconductor device according to claim 25, wherein the metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer, and the metallic layer is a tungsten layer.

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C<sup>6</sup>

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Cmcdi

29. (Amended) A semiconductor device with complementary MOS

transistors, each MOS transistor having a gate electrode, a source region and a drain region, wherein the gate electrode is provided as a stacked structure comprising a silicon layer, an uppermost metallic layer, a metal silicide layer provided on the silicon layer side and a metal nitride layer provided under the metallic layer side between the silicon layer and the metallic layer.

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C

31. (Amended) A semiconductor device according to claim 29, wherein the

metal silicide layer is a tungsten silicide layer, the metal nitride layer is a tungsten nitride layer, and the metallic layer is a tungsten layer.

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33. (Amended) A semiconductor device comprising on a substrate, at least

one MOS transistor, wherein a gate electrode of the MOS transistor is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a metal nitride layer and a metallic layer, formed in that order beginning with the silicon layer.

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